# 2SC5363

## Silicon NPN epitaxial planar type

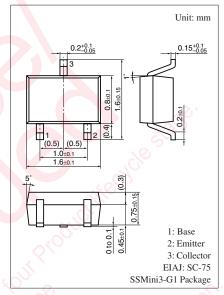
For low-voltage high-frequency amplification

#### ■ Features

- High transition frequency f<sub>T</sub>
- Small collector output capacitance (Common base, input open circuited) Cob
- SS-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing

### ■ Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	$V_{CBO}$	9	V	
Collector-emitter voltage (Base open)	$V_{CEO}$	6	V	
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	2	V	
Collector current	$I_{C}$	30	mA	
Collector power dissipation	$P_{C}$	125	mW	
Junction temperature	T <sub>j</sub>	125	°C	
Storage temperature	$T_{stg}$	-55 to +125	°C	

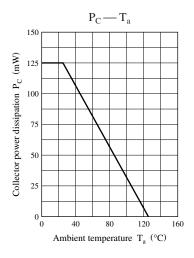


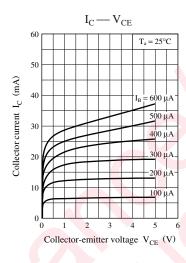
Marking Symbol: 3Y

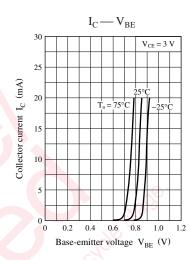
## ■ Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

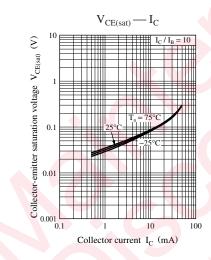
	Parameter	Symbol	Conditions	Min	Тур	Max	Unit
	Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 5 \text{ V}, I_{E} = 0$	10	250	1	μΑ
	Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 1 \text{ V}, I_C = 0$			1	μΑ
	Forward current transfer ratio	$h_{FE}$	$V_{CE} = 3 \text{ V}, I_{C} = 10 \text{ mA}$	40	100	160	_
	Transition frequency	$f_T$	$V_{CE} = 3 \text{ V}, I_{C} = 10 \text{ mA}, f = 1.5 \text{ GHz}$		10		GHz
	Collector output capacitance	C <sub>ob</sub>	$V_{CB} = 3 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$		0.4	0.7	pF
	(Common base, input open circuited)		7/10, 50,				
	Forward transfer gain	S <sub>21e</sub>   <sup>2</sup>	$V_{CE} = 0.3 \text{ V}, I_{C} = 1 \text{ mA}, f = 0.9 \text{ GHz}$		6.5		dB
_	Noise figure	NF	$V_{CE} = 0.3 \text{ V}, I_{C} = 1 \text{ mA}, f = 0.9 \text{ GHz}$		1.7		dB

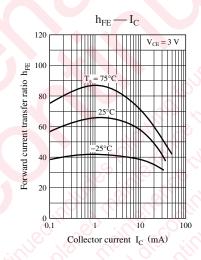
Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

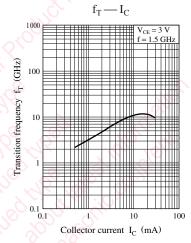


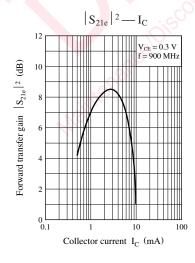


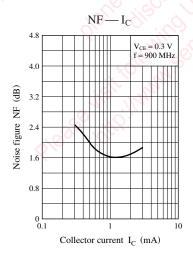


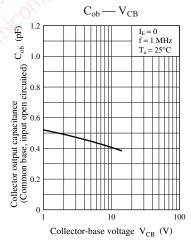












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